SN65HVD3080E SN65HVD3083E SN65HVD3086E





SLLS771B-NOVEMBER 2006-REVISED MARCH 2007

LOW-POWER RS-485 FULL-DUPLEX DRIVERS/RECEIVERS

FEATURES

- **Low Quiescent Power**
 - 375 µA (Typical) Enabled Mode
 - 2 nA (Typical) Shutdown Mode
- **Small MSOP Package**
- 1/8 Unit-Load—Up to 256 Nodes per Bus
- 16 kV Bus-Pin ESD Protection, 6 kV All Pins
- Failsafe Receiver (Bus Open, Short, Idle)
- **TIA/EIA-485A Standard Compliant**
- **RS-422 Compatible**

APPLICATIONS

- **Motion Controllers**
- Point-of-Sale (POS) Terminals
- **Rack-to-Rack Communications**
- **Industrial Networks**
- **Power Inverters**
- **Battery-Powered Applications**
- **Building Automation**

(TOP VIEW) RF DE GND

SN65HVD308xE

DEVICE	SIGNAL RATE
SN65HVD3080E	200 kbps
SN65HVD3083E	1 Mbps
SN65HVD3086E	20 Mbps

DESCRIPTION

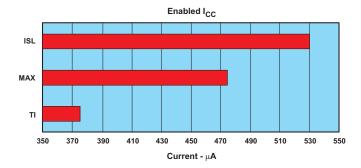
Each of these devices is a balanced driver and receiver designed for full-duplex RS-485 or RS-422 data bus networks. Powered by a 5-V supply, they are fully compliant with the TIA/EIA-485A standard.

With controlled bus output transition times, the devices are suitable for signaling rates from 200 kbps to 20 Mbps.

The devices are designed to operate with a low supply current, less than 1 mA (typical), exclusive of the load. When in the inactive shutdown mode, the supply current drops to a few nanoamps, making these devices ideal for power-sensitive applications.

The wide common-mode range and high ESD protection levels of these devices make them suitable for demanding applications such as motion controllers, electrical inverters, industrial networks, and cabled chassis interconnects where noise tolerance is essential.

These devices are characterized for operation over the temperature range -40°C to 85°C



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION

PART NUMBER	PACKAGE ⁽¹⁾	MARKED AS
SN65HVD3080E		BTT
SN65HVD3083E	DGS, DGSR ⁽²⁾	BTU
SN65HVD3086E		BTF

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

		UNIT
V _{CC}	Supply voltage range (2)	–0.3 V to 7 V
$V_{(A)}, V_{(B)}, V_{(Y)}, V_{(Z)}$	Voltage range at any bus terminal (A, B, Y, Z)	−9 V to 14 V
V _(TRANS)	Voltage input, transient pulse through 100 Ω . See Figure 10 (A, B, Y, Z)	–50 to 50 V
V_{I}	Input voltage range (D, DE, RE)	-0.3 V to V _{CC} +0.3 V
P_{D}	Continuous total power dissipation	See the dissipation rating table
T _J	Junction temperature	170°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

POWER DISSIPATION RATINGS

PACKAGE	ACKAGE T _A < 25°C DERATING ABOVE 1		T _A = 85°C
DGS-10	463 mW	3.71 mW/°C	241 mW

¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

ELECTROSTATIC DISCHARGE PROTECTION

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Human Body Model ⁽¹⁾	A,B,Y,Z, and GND		16k		V
	All pins		6k		V
Field-induced-Charged Device Mode (2)	All pins		1.5k		V
Machine Model			200		V

Tested in accordance JEDEC Standard 22, Test Method A114-A. Bus pin stressed with respect to a common connection of GND and V_{CC}.

⁽²⁾ The R suffix indicated tape and reel.

²⁾ All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

⁽²⁾ Tested in accordance JEDEC Standard 22, Test Method C101.

SN65HVD3080E



SUPPLY CURRENT

over recommended operating conditions unless otherwise noted

		PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		RE at 0 V, D and DE at V _{CC,} No load	Receiver enabled, Driver enabled		375	750	μΑ
		RE at 0 V, D and DE at 0 V, No load	Receiver enabled, Driver disabled		300	680	μΑ
ICC	Supply current	$\overline{\text{RE}}$ at V_{CC} , D and DE at V_{CC} , No load	Receiver disabled, Driver enabled		240	600	μΑ
		RE at V _{CC} , D and DE at 0 V, No load	Receiver disabled, Driver disabled		2	1000	nA

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range unless otherwise noted

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		4.5	5	5.5	
V_{I} or V_{IC}	Voltage at any bus terminal (separately or common mode)	-7 ⁽¹⁾		12	V
V _{IH}	High-level input voltage	D, DE, RE	2		V _{CC}	
V _{IL}	Low-level input voltage	D, DE, RE	0		0.8	V
V_{ID}	Differential input voltage		-12		12	
_	High lovel output ourrent	Driver	-60			A
IOH	High-level output current	Receiver	-10			mA
1	Low lovel cutout current	Driver			60	A
I _{OL}	Low-level output current	Receiver			10	mA
TJ	Junction temperature	Junction temperature			150	°C
T _A	Ambient still-air temperature		-40		85	-0

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.



DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		No load, I _O = 0	3	4.3	V_{CC}	
D.7. I	Differential automotivation	$R_L = 54 \Omega$, See Figure 1	1.5	2.3		V
V _{OD}	Differential output voltage	V _{test} = -7 V to 12 V, See Figure 2	1.5			V
		$R_L = 100 \Omega$, See Figure 1	2			
$\Delta V_{OD} $	Change in magnitude of differential output voltage	$R_L = 54 \Omega$, See Figure 1 and Figure 2	-0.2	0	0.2	V
V _{OC(SS)}	Steady-state common-mode output voltage		1	2.6	3	
$\Delta V_{OC(SS)}$	Common-mode output voltage (Dominant)	See Figure 3	-0.1	0	0.1	V
V _{OC(PP)}	Peak-to-peak common-mode output voltage			0.5		
		$V_{CC} = 0 \text{ V}, V_{(Z)} \text{ or } V_{(Y)} = 12 \text{ V}$ Other input at 0 V			1	
$I_{Z(Y)}$ or	High-impedance state output current	$V_{CC} = 0 \text{ V}, V_{(Z)} \text{ or } V_{(Y)} = -7 \text{ V}$ Other input at 0 V	-1			
$I_{Z(Z)}$		$V_{CC} = 5 \text{ V}, V_{(Z)} \text{ or } V_{(Y)} = 12 \text{ V}$ Other input at 0 V			1	Α
		$V_{CC} = 5 \text{ V}, V_{(Z)} \text{ or } V_{(Y)} = -7 \text{ V}$ Other input at 0 V	-1			
I _I	Input current	D, DE	-100		100	Α
Ios	Short-circuit output current	-7 V ≤ V _O ≤ 12 V	-250		250	mA

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	HVD3080E				0.7	1.3	μs
t _{PLH} , t _{PHL}		ropagation delay time, low-to-high-level output ropagation delay time, high-to-low-level output			150	500	ns
PHL	1 ropagation delay time, high to low level output	HVD3086E			12	20	ns
		HVD3080E	$R_1 = 54 \Omega$	0.5	0.9	1.5	μs
t _r , t _f	Differential output signal rise time Differential output signal fall time	HVD3083E	$C_{L} = 50 \text{ pF},$		200	300	ns
4	Differential output signal fall time	HVD3086E	See Figure 4		7	15	ns
		HVD3080E			20	200	ns
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	HVD3083E			5	50	ns
		HVD3086E			1.4	5	ns
	Propagation delay time, high-impedance-to-high-level output	HVD3080E	$R_L = 110 \Omega$		2.5	7	μs
t _{PZH}		HVD3083E			1	2.5	μs
		HVD3086E			13	30	ns
		HVD3080E	RE at 0 V, See Figure 5		80	200	ns
t_{PHZ}	Propagation delay time, high-level-to-high-impedance output	HVD3083E	3		60	100	ns
	riigh level to riigh impedance odiput	HVD3086E			12	30	ns
		HVD3080E			2.5	7	μs
t_{PZL}	Propagation delay time, high-impedance-to-low-level output	HVD3083E			1	2.5	μs
	odiput	HVD3086E	$R_L = 110 \Omega$		13	30	ns
		HVD3080E	RE at 0 V, See Figure 6		80	200	ns
t_{PLZ}	Propagation delay time, low-level-to-high-impedance output	HVD3083E			60	100	ns
	ouput	HVD3086E	1		12	30	ns
t _{PZH} ,	Propagation delay time, standby-to-high-level output (S	See Figure 5)	D 440 0 DE 40 V		0.5	_	
t _{PZL}	Propagation delay time, standby-to-low-level output (Se	ee Figure 6)	$R_L = 110 \Omega$, \overline{RE} at 3 V		3.5	7	μs

SN65HVD3080E SN65HVD3083E



RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETE	ER .	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
$V_{\text{IT+}}$	V _{IT+} Positive-going differential input threshold voltage I ₀		$I_{O} = -10 \text{ mA}$		-0.08	-0.01	
V _{IT-}	Negative-going differentia voltage	I input threshold	I _O = 10 mA	-0.2	-0.1		V
V_{hys}	Hysteresis voltage (V _{IT+} -	V _{IT-})			30		mV
V _{OH}			V _{ID} = 200 mV, I _{OH} = -10 mA, See Figure 7 and Figure 8	4	4.6		V
V _{OL}	DL Low-level output voltage		V _{ID} = -200 mV, I _{OH} = 10 mA, See Figure 7 and Figure 8		0.15	0.4	V
loz	High-impedance-state ou	tput current	$V_O = 0$ or V_{CC}	-1		1	Α
			V_A or $V_B = 12 \text{ V}$		0.04	0.11	
	Dua input aurrant	Other input at 01/	V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0 \text{ V}$		0.06	0.13	A
Ц	Bus input current	Other input at 0V	V_A or $V_B = -7 V$	-0.1	-0.04		mA
			V_A or $V_B = -7 V$, $V_{CC} = 0 V$	-0.05	-0.03		
I _{IH}	High-level input current		V _{IH} = 2 V	-60	-30		Α
I _{IL}	Low-level input current		V _{IL} = 0.8 V	-60	-30		Α
C_{ID}	Differential input capacita	nce	$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$		7		pF

⁽¹⁾ All typical values are at 25C and with a 3.3-V supply.

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output			75	100		
t _{PHL}	Propagation delay time, high-to-low-level output	T			79	100	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	$V_{ID} = -1.5 \text{ V to}$ $C_{I} = 15 \text{ pF}, \text{ Se}$	1.5 V, ee Figure 8		4	10	ns
t _r	Output signal rise time		oo riigaro o		1.5	3	
t _f	Output signal fall time				1.8	3	
	Output disable time to bink lavel		DE at 5 V, See Figure 9		5	50	ns
t _{PZH}	Output disable time to high level	From standby	DE at 5 V, See Figure 9		1.6	3.5	μs
t _{PHZ}	Output enable time from high level		DE at 5 V, See Figure 9		5	50	ns
	Output disable time to law level		DE at 0 V, See Figure 9		10	50	ns
t _{PZL}	Output disable time to low level	From standby	DE at 5 V, See Figure 9		1.7	3.5	μs
t _{PLZ}	Output enable time from low level		DE at 5 V, See Figure 9		8	50	ns



PARAMETER MEASUREMENT INFORMATION

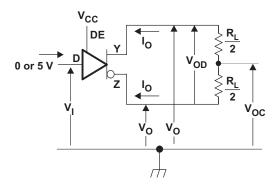


Figure 1. Driver V_{OD} Test Circuit and Current Definitions

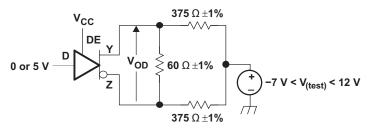


Figure 2. Driver V_{OD} With Common-Mode Loading Test Circuit

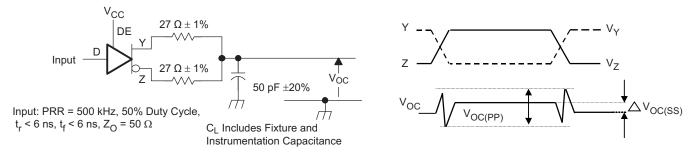


Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

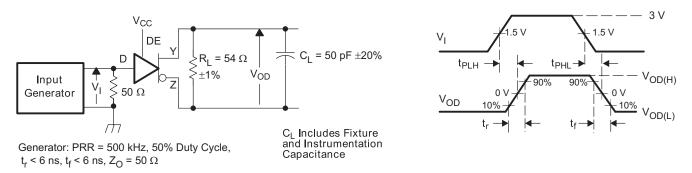


Figure 4. Driver Switching Test Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION (continued)

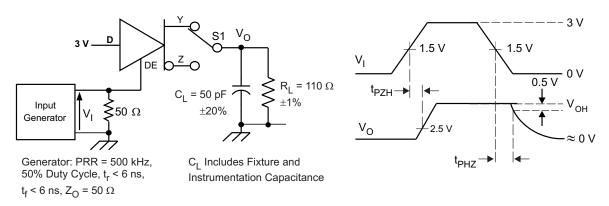


Figure 5. Driver High-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

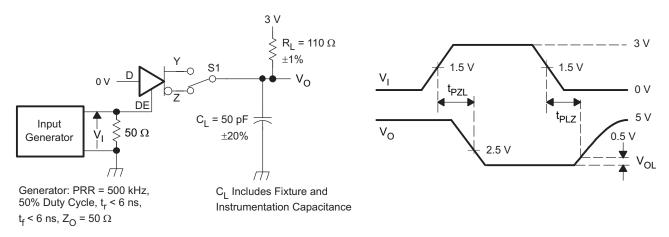


Figure 6. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

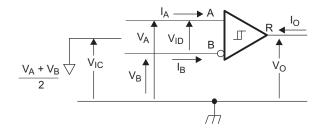


Figure 7. Receiver Voltage and Current Definitions

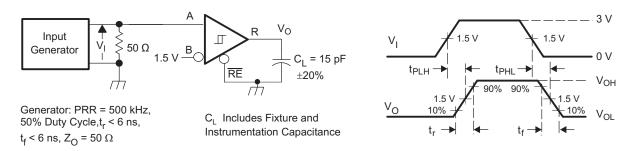


Figure 8. Receiver Switching Test Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION (continued)

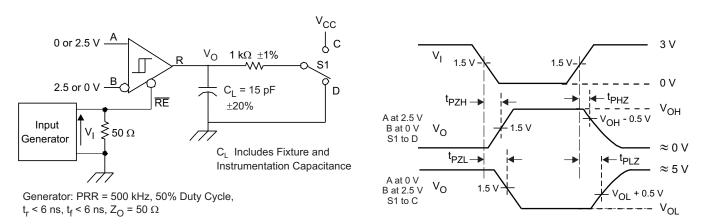
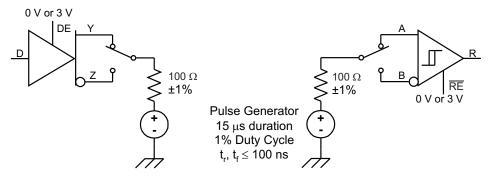


Figure 9. Receiver Enable and Disable Test Circuit and Voltage Waveforms



A. This test is conducted to test survivability only. Data stability at the R output is not specified.

Figure 10. Transient Overvoltage Test Circuit



DEVICE INFORMATION

FUNCTION TABLES

DRIVER⁽¹⁾

INPUT	Enable	OUTPUTS		
D	DE	Y	Z	
Н	Н	Н	L	
L	Н	L	Н	
Х	L	Z	Z	
Open	Н	Н	L	

(1) H = high level, L = low level, Z = high impedance, X = irrelevant, ? = indeterminate

RECEIVER(1)

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	ENABLE RE	OUTPUT R
V _{ID} ≤ -0.2 V	L	L
-0.2 V < V _{ID} < -0.01 V	L	?
-0.01 V ≤ V _{ID}	L	Н
X	Н	Z
Open Circuit	L	Н
BUS Idle	L	Н
Short Circuit	L	Н

⁽¹⁾ H = high level, L = low level, Z = high impedance, X = irrelevant, ? = indeterminate

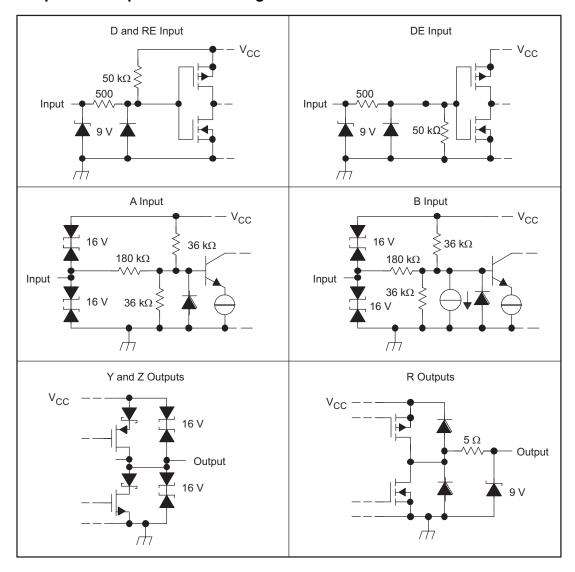
DEVICE ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P _(AVG)	Average power dissipation	R_L = 60 Ω , Input to D a 500-kHz 50% duty cycle square-wave	85	109	136	mW

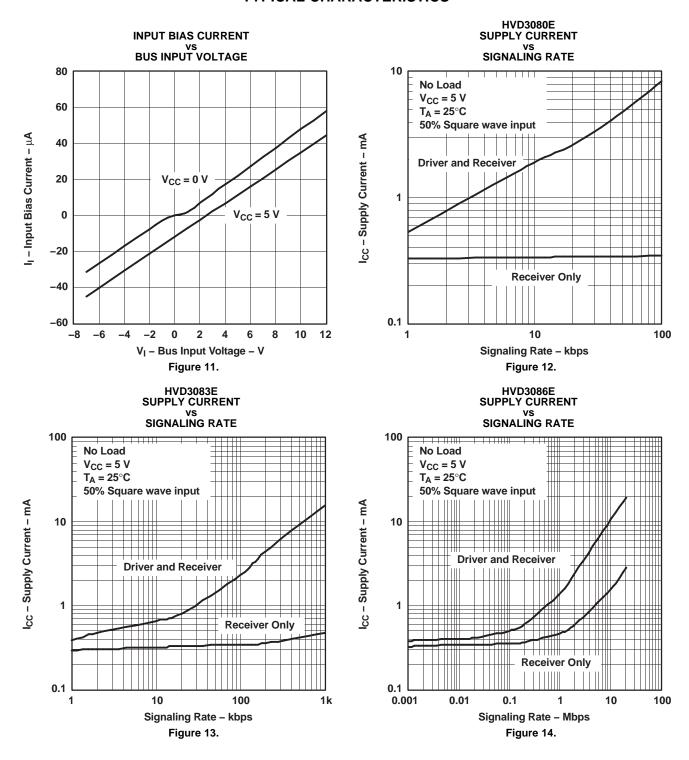


Equivalent Input and Output Schematic Diagrams



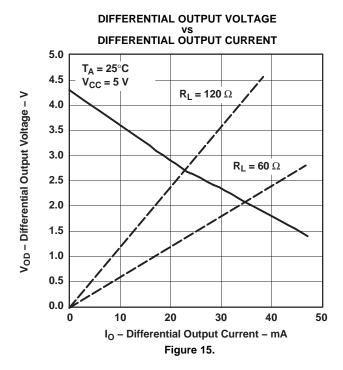


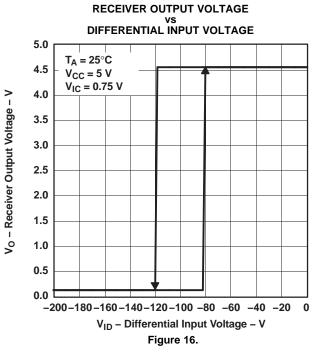
TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS (continued)







SN65HVD3080E





Changes from Revision A (December 2006) to Revision B				
•	Changed V _{OH} + 0.5 V to V _{OH} - 0.5 V in Figure 9		8	

PACKAGE OPTION ADDENDUM

www.ti.com 4-Jan-2010

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65HVD3080EDGS	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3080EDGSG4	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3080EDGSR	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3080EDGSRG4	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3083EDGS	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3083EDGSG4	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3083EDGSR	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3083EDGSRG4	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3086ED	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD3086EDGS	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3086EDGSG4	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3086EDGSR	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3086EDGSRG4	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65HVD3086EDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is



PACKAGE OPTION ADDENDUM

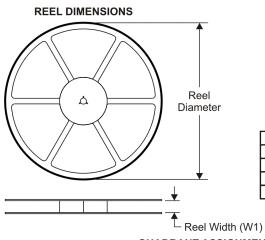
www.ti.com 4-Jan-2010

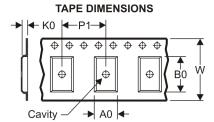
provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



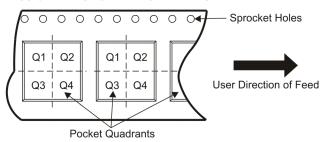
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

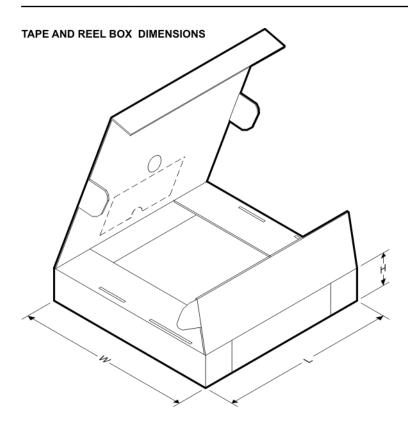
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD3080EDGSR	MSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65HVD3083EDGSR	MSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65HVD3086EDGSR	MSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1



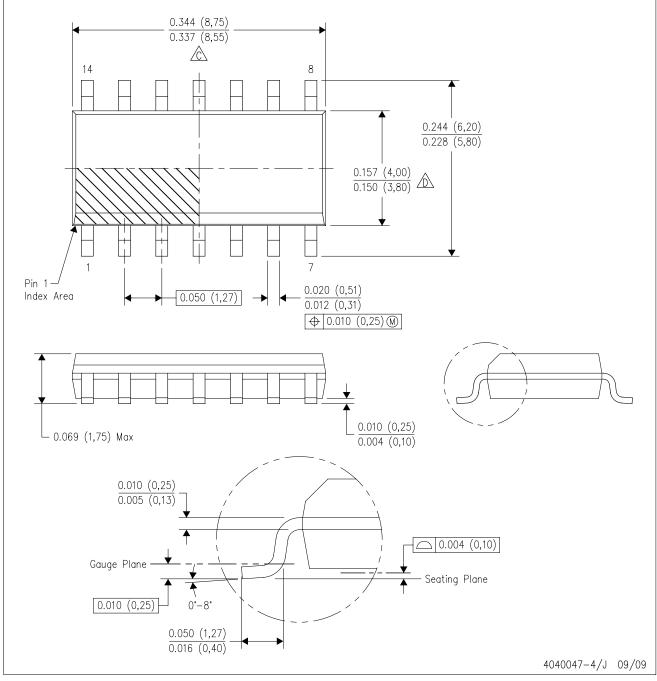


*All dimensions are nominal

7 til dillionolollo alo nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD3080EDGSR	MSOP	DGS	10	2500	346.0	346.0	29.0
SN65HVD3083EDGSR	MSOP	DGS	10	2500	346.0	346.0	29.0
SN65HVD3086EDGSR	MSOP	DGS	10	2500	346.0	346.0	29.0

D (R-PDSO-G14)

PLASTIC SMALL-OUTLINE PACKAGE



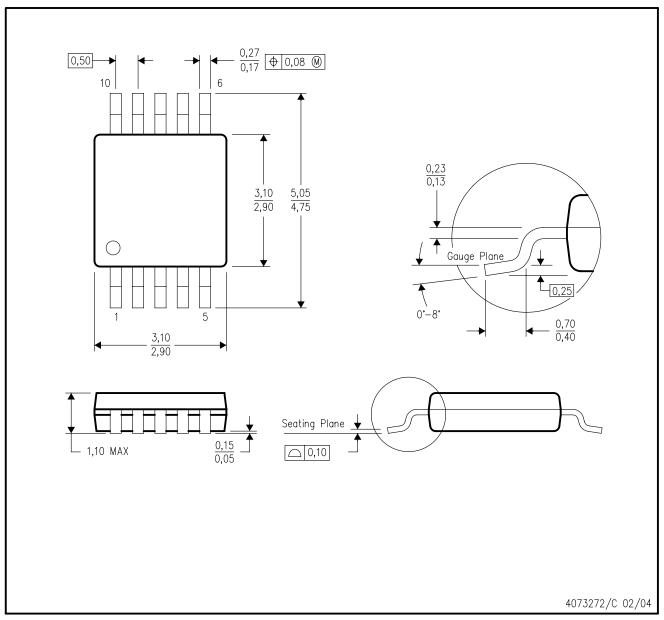
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AB.



DGS (S-PDSO-G10)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Applications Products Amplifiers amplifier.ti.com Audio www.ti.com/audio Data Converters Automotive www.ti.com/automotive dataconverter.ti.com DLP® Products Broadband www.dlp.com www.ti.com/broadband DSP Digital Control dsp.ti.com www.ti.com/digitalcontrol Clocks and Timers www.ti.com/clocks Medical www.ti.com/medical Military Interface www.ti.com/military interface.ti.com Optical Networking Logic logic.ti.com www.ti.com/opticalnetwork Power Mgmt power.ti.com Security www.ti.com/security Telephony Microcontrollers microcontroller.ti.com www.ti.com/telephony Video & Imaging www.ti-rfid.com www.ti.com/video RF/IF and ZigBee® Solutions www.ti.com/lprf Wireless www.ti.com/wireless

> Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2009, Texas Instruments Incorporated